

# Andr Vantomme

## List of Publications by Citations

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410  
papers

6,917  
citations

40  
h-index

63  
g-index

427  
ext. papers

7,459  
ext. citations

3.2  
avg, IF

5.34  
L-index

#	Paper	IF	Citations
410	Size-dependent optical properties of colloidal PbS quantum dots. <i>ACS Nano</i> , <b>2009</b> , 3, 3023-30	16.7	847
409	Binding of Phosphonic Acids to CdSe Quantum Dots: A Solution NMR Study. <i>Journal of Physical Chemistry Letters</i> , <b>2011</b> , 2, 145-152	6.4	207
408	Cooperative Catalysis for Multistep Biomass Conversion with Sn/Al Beta Zeolite. <i>ACS Catalysis</i> , <b>2015</b> , 5, 928-940	13.1	137
407	Semiconducting Mg <sub>2</sub> Si thin films prepared by molecular-beam epitaxy. <i>Physical Review B</i> , <b>1996</b> , 54, 16965-16971	3.3	109
406	Critical size for exchange bias in ferromagnetic-antiferromagnetic particles. <i>Applied Physics Letters</i> , <b>2005</b> , 87, 012501	3.4	98
405	Characterization of GeSn materials for future Ge pMOSFETs source/drain stressors. <i>Microelectronic Engineering</i> , <b>2011</b> , 88, 342-346	2.5	89
404	Compound Phase Formation in Thin Film Structures. <i>Critical Reviews in Solid State and Materials Sciences</i> , <b>1999</b> , 24, 1-62	10.1	85
403	Multiferroic BaTiO <sub>3</sub> /BiFeO <sub>3</sub> composite thin films and multilayers: strain engineering and magnetoelectric coupling. <i>Journal Physics D: Applied Physics</i> , <b>2014</b> , 47, 135303	3	83
402	Growth mechanism and continuity of atomic layer deposited TiN films on thermal SiO <sub>2</sub> . <i>Journal of Applied Physics</i> , <b>2002</b> , 92, 7641-7646	2.5	78
401	Direct Evidence for Tetrahedral Interstitial Er in Si. <i>Physical Review Letters</i> , <b>1997</b> , 79, 2069-2072	7.4	75
400	Crystalline Properties and Strain Relaxation Mechanism of CVD Grown GeSn. <i>ECS Journal of Solid State Science and Technology</i> , <b>2013</b> , 2, P134-P137	2	74
399	Independent tuning of size and coverage of supported Pt nanoparticles using atomic layer deposition. <i>Nature Communications</i> , <b>2017</b> , 8, 1074	17.4	72
398	An Inner-/Outer-Sphere Stabilized Sn Active Site in $\beta$ -Zeolite: Spectroscopic Evidence and Kinetic Consequences. <i>ACS Catalysis</i> , <b>2016</b> , 6, 31-46	13.1	67
397	Epitaxial CoSi <sub>2</sub> films on Si(100) by solid-phase reaction. <i>Journal of Applied Physics</i> , <b>1994</b> , 75, 3882-3891	2.5	66
396	Identification of the prime optical center in GaN:Eu <sup>3+</sup> . <i>Physical Review B</i> , <b>2010</b> , 81,	3.3	61
395	Concentration-controlled phase selection of silicide formation during reactive deposition. <i>Applied Physics Letters</i> , <b>1999</b> , 74, 3137-3139	3.4	58
394	Optical energies of AlInN epilayers. <i>Journal of Applied Physics</i> , <b>2008</b> , 103, 073510	2.5	56

393	Co silicide formation on SiGeC/Si and SiGe/Si layers. <i>Applied Physics Letters</i> , <b>1997</b> , 70, 1266-1268	3-4	55
392	Lattice location and stability of ion implanted Cu in Si. <i>Physical Review Letters</i> , <b>2000</b> , 84, 1495-8	7-4	55
391	Surface Chemistry of CuInS <sub>2</sub> Colloidal Nanocrystals, Tight Binding of L-Type Ligands. <i>Chemistry of Materials</i> , <b>2014</b> , 26, 5950-5957	9.6	53
390	Less is more. Cation exchange and the chemistry of the nanocrystal surface. <i>ACS Nano</i> , <b>2014</b> , 8, 7948-57	16.7	52
389	Tensile strained GeSn on Si by solid phase epitaxy. <i>Applied Physics Letters</i> , <b>2013</b> , 102, 052106	3-4	52
388	Thin film growth of semiconducting Mg <sub>2</sub> Si by codeposition. <i>Applied Physics Letters</i> , <b>1997</b> , 70, 1086-1088	3-4	52
387	Position-sensitive Si pad detectors for electron emission channeling experiments. <i>Nuclear Instruments and Methods in Physics Research, Section A: Accelerators, Spectrometers, Detectors and Associated Equipment</i> , <b>2004</b> , 524, 245-256	1.2	50
386	Correlation of magnetoelectric coupling in multiferroic BaTiO <sub>3</sub> -BiFeO <sub>3</sub> superlattices with oxygen vacancies and antiphase octahedral rotations. <i>Applied Physics Letters</i> , <b>2015</b> , 106, 012905	3-4	49
385	Damage and strain in epitaxial GeSi <sub>1-x</sub> films irradiated with Si. <i>Journal of Applied Physics</i> , <b>1993</b> , 74, 6039-6045	6.45	49
384	Size-Dependent Optical Properties of Zinc Blende Cadmium Telluride Quantum Dots. <i>Journal of Physical Chemistry C</i> , <b>2012</b> , 116, 5049-5054	3.8	48
383	Emission channeling studies of Pr in GaN. <i>Journal of Applied Physics</i> , <b>2000</b> , 88, 1319-1324	2.5	48
382	Defect accumulation during channeled erbium implantation into GaN. <i>Journal of Applied Physics</i> , <b>2005</b> , 98, 123504	2.5	47
381	Growth mechanism and optical properties of semiconducting Mg <sub>2</sub> Si thin films. <i>Microelectronic Engineering</i> , <b>2000</b> , 50, 237-242	2.5	46
380	Hydrogen-induced Ostwald ripening at room temperature in a Pd nanocluster film. <i>Physical Review Letters</i> , <b>2008</b> , 100, 236105	7-4	44
379	Pt redistribution during Ni(Pt) silicide formation. <i>Applied Physics Letters</i> , <b>2008</b> , 93, 261912	3-4	43
378	Comparison of the properties of GaN grown on complex Si-based structures. <i>Applied Physics Letters</i> , <b>2005</b> , 86, 081912	3-4	43
377	Direct evidence of spontaneous quantum dot formation in a thick InGaN epilayer. <i>Applied Physics Letters</i> , <b>2000</b> , 77, 507-509	3-4	43
376	Tailored Ag-Cu-Mg multielemental nanoparticles for wide-spectrum antibacterial coating. <i>Nanoscale</i> , <b>2019</b> , 11, 1626-1635	7.7	42

375	Electron emission channeling with position-sensitive detectors. <i>Nuclear Instruments &amp; Methods in Physics Research B</i> , <b>1998</b> , 136-138, 744-750	1.2	42
374	High-precision determination of lattice constants and structural characterization of InN thin films. <i>Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films</i> , <b>2006</b> , 24, 275-279	2.9	42
373	Self-diffusion of iron in L10-ordered FePt thin films. <i>Physical Review B</i> , <b>2006</b> , 74,	3.3	42
372	Magnetotransport in epitaxial thin films of the magnetic perovskite Pr <sub>0.5</sub> Sr <sub>0.5</sub> MnO <sub>3</sub> . <i>Physical Review B</i> , <b>1997</b> , 55, 3699-3707	3.3	40
371	Lattice location and optical activation of rare earth implanted GaN. <i>Materials Science and Engineering B: Solid-State Materials for Advanced Technology</i> , <b>2003</b> , 105, 132-140	3.1	40
370	Tuning quantum corrections and magnetoresistance in ZnO nanowires by ion implantation. <i>Nano Letters</i> , <b>2012</b> , 12, 666-72	11.5	38
369	Elastic strain in In <sub>0.18</sub> Ga <sub>0.82</sub> N layer: A combined x-ray diffraction and Rutherford backscattering/channeling study. <i>Applied Physics Letters</i> , <b>1999</b> , 74, 365-367	3.4	38
368	Carrier density variation in films of Nd <sub>0.5</sub> Sr <sub>0.5</sub> MnO <sub>3</sub> . <i>Europhysics Letters</i> , <b>1998</b> , 41, 49-54	1.6	37
367	Practical limits for detection of ferromagnetism using highly sensitive magnetometry techniques. <i>Journal Physics D: Applied Physics</i> , <b>2011</b> , 44, 215001	3	33
366	Low-energy heavy-ion TOF-ERDA setup for quantitative depth profiling of thin films. <i>Nuclear Instruments &amp; Methods in Physics Research B</i> , <b>2008</b> , 266, 5144-5150	1.2	33
365	Hyperthermal effects on nucleation and growth during low-energy ion deposition. <i>Physical Review B</i> , <b>2002</b> , 65,	3.3	33
364	The van der Waals epitaxial growth of GaSe on Si(111). <i>Journal of Applied Physics</i> , <b>1997</b> , 81, 7289-7294	2.5	32
363	Searching for room temperature ferromagnetism in transition metal implanted ZnO and GaN. <i>Journal of Applied Physics</i> , <b>2013</b> , 113, 023903	2.5	31
362	H <sub>2</sub> S exposure of a (100)Ge surface: Evidences for a (2×1) electrically passivated surface. <i>Applied Physics Letters</i> , <b>2007</b> , 90, 222105	3.4	31
361	Aligned and twinned orientations in epitaxial CoSi <sub>2</sub> layers. <i>Applied Physics Letters</i> , <b>1990</b> , 57, 135-137	3.4	31
360	Initial growth mechanism of atomic layer deposited TiN. <i>Applied Physics Letters</i> , <b>2004</b> , 84, 4571-4573	3.4	30
359	Lattice Location of Mg in GaN: A Fresh Look at Doping Limitations. <i>Physical Review Letters</i> , <b>2017</b> , 118, 095501	7.4	29
358	Relaxor ferroelectricity and magnetoelectric coupling in ZnO-Co nanocomposite thin films: beyond multiferroic composites. <i>ACS Applied Materials &amp; Interfaces</i> , <b>2014</b> , 6, 4737-42	9.5	29

357	Implantation-induced damage in Ge: strain and disorder profiles during defect accumulation and recovery. <i>Journal Physics D: Applied Physics</i> , <b>2009</b> , 42, 165404	3	29
356	Ge <sub>1-x</sub> Sn <sub>x</sub> stressors for strained-Ge CMOS. <i>Solid-State Electronics</i> , <b>2011</b> , 60, 53-57	1.7	28
355	Er-defect complexes and isolated Er center spectroscopy in Er-implanted GaN. <i>Materials Science and Engineering B: Solid-State Materials for Advanced Technology</i> , <b>2003</b> , 105, 101-105	3.1	28
354	The dependence of the optical energies on InGaN composition. <i>Materials Science and Engineering B: Solid-State Materials for Advanced Technology</i> , <b>2001</b> , 82, 194-196	3.1	28
353	Suppression of rare-earth implantation-induced damage in GaN. <i>Nuclear Instruments &amp; Methods in Physics Research B</i> , <b>2001</b> , 175-177, 148-153	1.2	28
352	Formation of buried and surface CoSi <sub>2</sub> layers by ion implantation. <i>Nuclear Instruments &amp; Methods in Physics Research B</i> , <b>1990</b> , 45, 658-663	1.2	28
351	PbS/CdS Core/Shell Quantum Dots by Additive, Layer-by-Layer Shell Growth. <i>Chemistry of Materials</i> , <b>2016</b> , 28, 6953-6959	9.6	27
350	Transition metal impurities on the bond-centered site in germanium. <i>Physical Review Letters</i> , <b>2009</b> , 102, 065502	7.4	27
349	Interplay between structural and magnetic properties of L10-FePt(001) thin films directly grown on MgO(001). <i>Journal of Applied Physics</i> , <b>2009</b> , 105, 073913	2.5	27
348	Structural and Magnetic Ordering of Chromium in Ag/Cr Multilayers. <i>Physical Review Letters</i> , <b>1998</b> , 81, 2562-2565	7.4	27
347	Antiparallel crystal orientation in CoSi <sub>2</sub> epitaxial bilayers formed by ion implantation. <i>Applied Physics Letters</i> , <b>1990</b> , 57, 1973-1975	3.4	26
346	The influence of interface roughness on the magnetic properties of exchange biased CoO/Fe thin films. <i>Journal of Applied Physics</i> , <b>2010</b> , 107, 113907	2.5	25
345	A simplified collisional model of sputtering in the linear cascade regime. <i>Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films</i> , <b>1997</b> , 15, 1976-1989	2.9	25
344	Enhancement of ALD TiN growth on SiO <sub>2</sub> and SiC:H films by O <sub>2</sub> -based plasma treatments. <i>Microelectronic Engineering</i> , <b>2002</b> , 60, 59-69	2.5	25
343	Epitaxial Coherence at Interfaces as Origin of High Magnetoelectric Coupling in Multiferroic BaTiO <sub>3</sub> /BiFeO <sub>3</sub> Superlattices. <i>Advanced Materials Interfaces</i> , <b>2016</b> , 3, 1500822	4.6	25
342	A Case Study of ALD Encapsulation of Quantum Dots: Embedding Supported CdSe/CdS/ZnS Quantum Dots in a ZnO Matrix. <i>Journal of Physical Chemistry C</i> , <b>2016</b> , 120, 18039-18045	3.8	25
341	Annealing effect on the optical properties and interdiffusion of MgO/Zr/MgO multilayered selective solar absorber coatings. <i>Solar Energy</i> , <b>2015</b> , 120, 123-130	6.8	24
340	Electric Field-Induced Oxidation of Ferromagnetic/Ferroelectric Interfaces. <i>Advanced Functional Materials</i> , <b>2014</b> , 24, 71-76	15.6	24

339	Lattice location study of implanted In in Ge. <i>Journal of Applied Physics</i> , <b>2009</b> , 105, 083522	2.5	24
338	Defects induced in GaN by europium implantation. <i>Applied Physics Letters</i> , <b>2004</b> , 85, 2244-2246	3.4	24
337	Importance of channeled implantation to the synthesis of erbium silicide layers. <i>Applied Physics Letters</i> , <b>1995</b> , 67, 3886-3888	3.4	24
336	Surface Chemistry of CdTe Quantum Dots Synthesized in Mixtures of Phosphonic Acids and Amines: Formation of a Mixed Ligand Shell. <i>Journal of Physical Chemistry C</i> , <b>2013</b> , 117, 13936-13943	3.8	23
335	Lattice location study of ion implanted Sn and Sn-related defects in Ge. <i>Physical Review B</i> , <b>2010</b> , 81,	3.3	23
334	The influence of Pt redistribution on Ni <sub>1-x</sub> Pt <sub>x</sub> Si growth properties. <i>Journal of Applied Physics</i> , <b>2010</b> , 108, 043505	2.5	23
333	Direct identification of interstitial Mn in heavily p-type doped GaAs and evidence of its high thermal stability. <i>Applied Physics Letters</i> , <b>2011</b> , 98, 201905	3.4	23
332	Dependence of the sticking coefficient of sputtered atoms on the target-substrate distance. <i>Journal Physics D: Applied Physics</i> , <b>2008</b> , 41, 152005	3	23
331	Depth dependence of the tetragonal distortion of a GaN layer on Si(111) studied by Rutherford backscattering/channeling. <i>Applied Physics Letters</i> , <b>2002</b> , 80, 4130-4132	3.4	23
330	Lattice location of implanted Cu in highly doped Si. <i>Applied Physics Letters</i> , <b>2000</b> , 77, 2142-2144	3.4	23
329	Comprehensive Rutherford backscattering and channeling study of ion-beam-synthesized ErSi <sub>1.7</sub> layers. <i>Journal of Applied Physics</i> , <b>1996</b> , 79, 6920-6925	2.5	23
328	Magnetic spin structure and magnetoelectric coupling in BiFeO <sub>3</sub> -BaTiO <sub>3</sub> multilayer. <i>Applied Physics Letters</i> , <b>2015</b> , 106, 082904	3.4	22
327	Mixed Zn and O substitution of Co and Mn in ZnO. <i>Physical Review B</i> , <b>2011</b> , 84,	3.3	22
326	Formation of Ni(Ge <sub>1-x</sub> Sn <sub>x</sub> ) layers with solid-phase reaction in Ni/Ge <sub>1-x</sub> Sn <sub>x</sub> /Ge systems. <i>Solid-State Electronics</i> , <b>2011</b> , 60, 46-52	1.7	22
325	Investigation of Ni fully silicided gates for sub-45 nm CMOS technologies. <i>Microelectronic Engineering</i> , <b>2004</b> , 76, 349-353	2.5	22
324	Artificial neural networks for instantaneous analysis of real-time Rutherford backscattering spectra. <i>Nuclear Instruments &amp; Methods in Physics Research B</i> , <b>2010</b> , 268, 1676-1681	1.2	21
323	Formation of epitaxial CoSi <sub>2</sub> on Si(100): Role of the annealing ambient. <i>Applied Physics Letters</i> , <b>1993</b> , 62, 243-245	3.4	21
322	Multidimensional Purcell effect in an ytterbium-doped ring resonator. <i>Nature Photonics</i> , <b>2016</b> , 10, 385-388	3.9	21

321	Extended X-ray absorption fine structure investigation of Sn local environment in strained and relaxed epitaxial Ge <sub>1-x</sub> Sn <sub>x</sub> films. <i>Journal of Applied Physics</i> , <b>2015</b> , 117, 095702	2.5	20
320	Improving the magnetic properties of Co-CoO systems by designed oxygen implantation profiles. <i>ACS Applied Materials &amp; Interfaces</i> , <b>2013</b> , 5, 4320-7	9.5	20
319	Spacious and mechanically flexible mesoporous silica thin film composed of an open network of interlinked nanoslabs. <i>Journal of Materials Chemistry</i> , <b>2011</b> , 21, 7692		20
318	Modulation of the workfunction of Ni fully silicided gates by doping: dielectric and silicide phase effects. <i>IEEE Electron Device Letters</i> , <b>2006</b> , 27, 99-101	4.4	20
317	Direct evidence for implanted Fe on substitutional Ga sites in GaN. <i>Applied Physics Letters</i> , <b>2001</b> , 78, 3217-3219	3.4	20
316	Ion-induced roughening and ripple formation on polycrystalline metallic films. <i>New Journal of Physics</i> , <b>2013</b> , 15, 093047	2.9	19
315	Exchange bias by implantation of O ions into Co thin films. <i>Applied Physics Letters</i> , <b>2010</b> , 96, 132503	3.4	19
314	Spin structure in perpendicularly magnetized Fe-FePt bilayers. <i>Physical Review B</i> , <b>2010</b> , 82,	3.3	19
313	On the thermal expansion coefficient of CoSi <sub>2</sub> and NiSi <sub>2</sub> . <i>Journal Physics D: Applied Physics</i> , <b>2009</b> , 42, 235402	3	19
312	Mössbauer Spectroscopy of Fe in Silicon with the Novel Laser-Ionized 57Mn <sup>+</sup> Ion Beam at Isolde. <i>Materials Science Forum</i> , <b>1997</b> , 258-263, 437-442	0.4	19
311	Trends in sputter yield data in the film deposition regime. <i>Physical Review B</i> , <b>2000</b> , 61, 8516-8525	3.3	19
310	Controlling the formation and stability of ultra-thin nickel silicides - An alloying strategy for preventing agglomeration. <i>Journal of Applied Physics</i> , <b>2018</b> , 123, 075303	2.5	18
309	50 years of ion channeling in materials science. <i>Nuclear Instruments &amp; Methods in Physics Research B</i> , <b>2016</b> , 371, 12-26	1.2	18
308	Rotatable anisotropy driven training effects in exchange biased Co/CoO films. <i>Journal of Applied Physics</i> , <b>2014</b> , 115, 243903	2.5	18
307	Atomic Layer Deposition of High-Dielectrics on Sulphur-Passivated Germanium. <i>Journal of the Electrochemical Society</i> , <b>2011</b> , 158, H687	3.9	18
306	The role of lattice mismatch and kinetics in texture development: Co <sub>1-x</sub> Ni <sub>x</sub> Si <sub>2</sub> thin films on Si(100). <i>Journal of Applied Physics</i> , <b>2008</b> , 103, 063506	2.5	18
305	Experimental and theoretical study of Ge surface passivation. <i>Microelectronic Engineering</i> , <b>2007</b> , 84, 2267-2273	3.2	18
304	Interpreting Mössbauer spectra reflecting an infinite number of sites: An application to Fe <sub>1-x</sub> Si <sub>x</sub> synthesized by pulsed laser annealing. <i>Physical Review B</i> , <b>2006</b> , 74,	3.3	18



303	Strain and orientation in epitaxial CoSi <sub>2</sub> (111) layers formed by ion implantation. <i>Nuclear Instruments &amp; Methods in Physics Research B</i> , <b>1991</b> , 54, 444-452	1.2	18
302	Interdependence between training and magnetization reversal in granular Co-CoO exchange bias systems. <i>Physical Review B</i> , <b>2014</b> , 89,	3.3	17
301	Diluted manganese on the bond-centered site in germanium. <i>Applied Physics Letters</i> , <b>2010</b> , 97, 151914	3.4	17
300	Influence of finite size effects on exchange anisotropy in oxidized Co nanocluster assembled films. <i>Physical Review B</i> , <b>2006</b> , 73,	3.3	17
299	Step decoration during deposition of Co on Ag(001) by ultralow energy ion beams. <i>Applied Physics Letters</i> , <b>1999</b> , 75, 938-940	3.4	17
298	Crystalline quality and phase stability of hexagonal GdSi <sub>1.7</sub> layers formed by channeled ion-beam synthesis. <i>Applied Physics Letters</i> , <b>1996</b> , 68, 3260-3262	3.4	17
297	X-ray-diffraction study of quasipseudomorphic ErSi <sub>1.7</sub> layers formed by channeled ion-beam synthesis. <i>Journal of Applied Physics</i> , <b>1996</b> , 80, 5713-5717	2.5	17
296	Induced ferromagnetism and magnetoelectric coupling in ion-beam synthesized BiFeO <sub>3</sub> /Fe <sub>2</sub> O <sub>4</sub> nanocomposite thin films. <i>Journal Physics D: Applied Physics</i> , <b>2016</b> , 49, 325302	3	15
295	Influence of O and C co-implantation on the lattice site of Er in GaN. <i>Applied Physics Letters</i> , <b>2004</b> , 84, 4304-4306	3.4	15
294	Influence of the implantation angle on the generation of defects for Er implanted GaN. <i>Nuclear Instruments &amp; Methods in Physics Research B</i> , <b>2003</b> , 206, 95-98	1.2	15
293	Interface and bulk properties of Fe/Mn sandwich structures. <i>Physical Review B</i> , <b>2003</b> , 67,	3.3	15
292	Cubic metastable FeSi <sub>1-x</sub> epitaxially grown on Si and MgO substrates. <i>Applied Surface Science</i> , <b>1995</b> , 91, 72-76	6.7	15
291	Reactive deposition epitaxy of CrSi <sub>2</sub> . <i>Applied Surface Science</i> , <b>1993</b> , 73, 146-152	6.7	15
290	Tailoring the magnetic anisotropy, magnetization reversal, and anisotropic magnetoresistance of Ni films by ion sputtering. <i>Physical Review B</i> , <b>2015</b> , 91,	3.3	14
289	Dynamical properties of ordered FePt alloys. <i>Journal of Alloys and Compounds</i> , <b>2015</b> , 651, 528-536	5.7	14
288	Mesoporous Oxide-Diluted Magnetic Semiconductors Prepared by Co Implantation in Nanocast 3D-Ordered In <sub>2</sub> O <sub>3</sub> Materials. <i>Journal of Physical Chemistry C</i> , <b>2013</b> , 117, 17084-17091	3.8	14
287	On the growth kinetics of Ni(Pt) silicide thin films. <i>Journal of Applied Physics</i> , <b>2013</b> , 113, 163504	2.5	14
286	Structural and Optical Properties of Amorphous and Crystalline GeSn Layers on Si. <i>ECS Journal of Solid State Science and Technology</i> , <b>2014</b> , 3, P403-P408	2	14



285	Determination of the dominant diffusing species during nickel and palladium germanide formation. <i>Thin Solid Films</i> , <b>2012</b> , 526, 261-268	2.2	14
284	Evidence of N substitution by Mn in GaN. <i>Physical Review B</i> , <b>2012</b> , 86,	3.3	14
283	Atomic-scale modification of hybrid FePt cluster-assembled films. <i>Physical Review B</i> , <b>2006</b> , 73,	3.3	14
282	Electrical characterization of defects introduced in n-type Ge during indium implantation. <i>Applied Physics Letters</i> , <b>2006</b> , 89, 152123	3.4	14
281	Metastable iron silicide phase formation by pulsed laser annealing. <i>Journal of Applied Physics</i> , <b>2004</b> , 95, 2365-2370	2.5	14
280	Extreme lowering of the Debye temperature of Sn nanoclusters embedded in thermally grown SiO <sub>2</sub> by low-lying vibrational surface modes. <i>Physical Review B</i> , <b>2004</b> , 70,	3.3	14
279	Stable and metastable iron silicide phases on Si(100). <i>Surface Science</i> , <b>2005</b> , 599, 122-127	1.8	14
278	Correlation of High Magnetoelectric Coupling with Oxygen Vacancy Superstructure in Epitaxial Multiferroic BaTiO <sub>3</sub> /BiFeO <sub>3</sub> Composite Thin Films. <i>Materials</i> , <b>2016</b> , 9,	3.5	14
277	Phase formation and texture of thin nickel germanides on Ge(001) and Ge(111). <i>Journal of Applied Physics</i> , <b>2016</b> , 119, 135305	2.5	14
276	Tuning the ferromagnetic-antiferromagnetic interfaces of granular Co-CoO exchange bias systems by annealing. <i>Journal of Applied Physics</i> , <b>2014</b> , 115, 133915	2.5	13
275	Adsorption of O <sub>2</sub> on Ge(100): Atomic Geometry and Site-Specific Electronic Structure. <i>Journal of Physical Chemistry C</i> , <b>2012</b> , 116, 9925-9929	3.8	13
274	Sn diffusion during Ni germanide growth on Ge <sub>1-x</sub> Sn <sub>x</sub> . <i>Applied Physics Letters</i> , <b>2011</b> , 99, 211905	3.4	13
273	Nucleation and diffusion during growth of ternary Co <sub>1-x</sub> Ni <sub>x</sub> Si <sub>2</sub> thin films studied by complementary techniques in real time. <i>Journal of Applied Physics</i> , <b>2008</b> , 104, 093533	2.5	13
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